



by a sacrificial material;

forming one or more holes in said sealed cavity;

introducing a non-liquid etchant into said sealed cavity through said one or more

holes using a barrel etcher, said structural material and said sacrificial material having

a high etch rate differential with respect to said etchant, such that said sacrificial

material is removed; and

sealing said one or more holes in said sealed cavity.

- Please re-write claim 2 as follows:

2. The method of claim 1 further comprising the step of choosing said etchant to etch said sacrificial material without substantially etching said substrate or said microstructure..

- Please re-write claim 4 as follows:

4. The method of claim 2 wherein said etchant is oxygen plasma, said sacrificial material is photoresist and wherein said structural material is aluminum.

- Please delete claims 5-20.
- Please add claims 21-23:

21. The method of claim 1 wherein said etchant has a high etch rate with respect to said sacrificial material and a low etch rate with respect to said structural material.

22. The method of claim 21 wherein said structural material is resistant to said etchant.

23. The method of claim 21 wherein said structural material is self-passivating with respect to said etchant.

REMARKS

In paragraph 1 under the Drawing section, the Examiner has objected to the drawings as failing to comply with 37 C.F.R. § 1.84 (p)(5) because they do not include reference numbers 7 and 9 used on page 4, line 30. In response, the Applicant has modified page 4, lines 7 and 9 to remove the offending reference numbers.